

3. (Amended) The hot plate for a semiconductor producing/examining device
according to claim 1,

wherein said ceramic substrate is subjected to an annealing treatment.

4. (Amended) The hot plate for a semiconductor producing/examining device
according to claim 1,

wherein said ceramic substrate is subjected to a cold isostatic pressing process before
it is sintered.

Please add new claims 5-8 as follows:

5. The hot plate for a semiconductor producing/examining device according to claim
2,

wherein said ceramic substrate is subjected to an annealing treatment.

6. (New) The hot plate for a semiconductor producing/examining device according
to claim 2,

wherein said ceramic substrate is subjected to a cold isostatic pressing process before
it is sintered.

7. (New) The hot plate for a semiconductor producing/examining device according
to claim 3,

wherein said ceramic substrate is subjected to a cold isostatic pressing process before
it is sintered.

8. (New) The hot plate for a semiconductor producing/examining device according
to claim 5,